

L-53P3BT

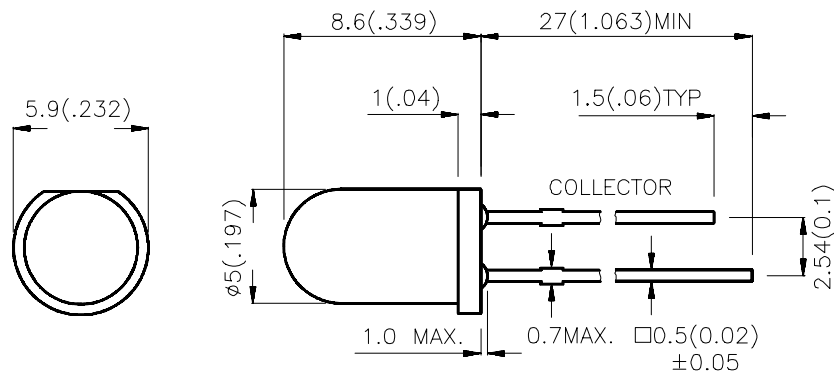
Features

- MECHANICALLY AND SPECTRALLY MATCHED TO THE L-53 SERIES INFRARED EMITTING LED LAMP.
- BLUE TRANSPARENT LENS.

Description

P3 Made with NPN silicon phototransistor chips.

Package Dimensions



Notes:

1. All dimensions are in millimeters (inches).
2. Tolerance is $\pm 0.25(0.01)$ " unless otherwise noted.
3. Lead spacing is measured where the lead emerge package.
4. Specifications are subject to change without notice.

Electrical / Optical Characteristics at $T_A=25^\circ\text{C}$

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Condition
$V_{BR\ CE0}$	Collector-to-Emitter Breakdown Voltage	30	-	-	V	$I_C=100\mu\text{A}$, $I_B=0$
$V_{BR\ EC0}$	Emitter-to-Collector Breakdown Voltage	5	-	-	V	$I_E=100\mu\text{A}$, $I_B=0$
$V_{CE(SAT)}$	Collector-to-Emitter Saturation Voltage	-	-	0.8	V	$I_C=0.1\text{mA}$, $H=2.5\text{mW/cm}^2$
I_{CE0}	Collector Dark Current	-	-	100	nA	$V_{CE}=10\text{V}$, $H=0\text{mW/cm}^2$
T_R	Rise Time (10% to 90%)	-	3	-	μs	$V_{CE}=5\text{V}$, $I_C=1\text{mA}$, $R_L=100\Omega$
T_F	Fall Time (90% to 10%)	-	3	-	μs	
$I_{(ON)}$	On State Collector Current	0.7	3.0	-	mA	$V_{CE}=5\text{V}$, $E_e=1\text{mW/cm}^2$, $\lambda=940\text{nm}$

Absolute Maximum Ratings at $T_A=25^\circ\text{C}$

Parameter	Maximum Rating
Collector-to-Emitter Breakdown Voltage	30V
Emitter-to-Collector Breakdown Voltage	5V
Power dissipation	100mW
Operating Temperature	-40°C To $+85^\circ\text{C}$
Storage Temperature	-40°C To $+85^\circ\text{C}$
Lead Solder Temperature [1]	260°C For 5 Seconds

Note:

1. 2mm below package base.

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